

DCR818SG

Phase Control Thyristor

Supersedes October 2000 version, DS4241-5.1

DS4241-6.0 July 2001

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- DC Motor Control
- Welding
- Battery Chargers

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V _{DRM} V _{RRM} V	Conditions
DCR818SG48	4800	$T_{v_i} = 0^{\circ} \text{ to } 125^{\circ}\text{C},$
DCR818SG47	4700	$I_{DRM}^{v_j} = I_{RRM} = 75 \text{mA},$
DCR818SG46	4600	V_{DRM} , V_{RRM} $t_p = 10ms$,
DCR818SG45	4500	V _{DSM} & V _{RSM} =
DCR818SG44	4400	V _{DRM} & V _{RRM} + 100V
		Respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR818SG46

Note: Please use the complete part number when ordering and quote this number in any future correspondance relating to your order.

KEY PARAMETERS

 V_{DRM} 4800V $I_{T(AV)}$ 529A I_{TSM} 7500A $dVdt^*$ 1000V/ μ s dI/dt 150A/ μ s

*Higher dV/dt selections available

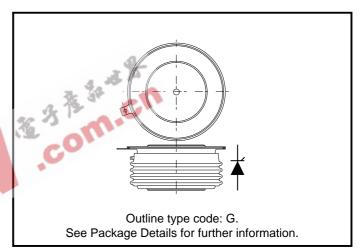


Fig.1 Package outline



CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units			
Double Sid	Double Side Cooled						
I _{T(AV)}	Mean on-state current	Half wave resistive load	529	А			
I _{T(RMS)}	RMS value	-	830	А			
I _T	Continuous (direct) on-state current	-	756	А			
Single Side Cooled (Anode side)							
I _{T(AV)}	Mean on-state current	Half wave resistive load	349	А			
I _{T(RMS)}	RMS value	-	548	А			
I _T	Continuous (direct) on-state current		464	А			

CURRENT RATINGS

I _T	Continuous (direct) on-state current		464	Α
	Γ RATINGS unless stated otherwise	3 tom.cn		
Symbol	Parameter	Conditions	Max.	Units
Double Sid	de Cooled			
I _{T(AV)}	Mean on-state current	Half wave resistive load	425	А
I _{T(RMS)}	RMS value	-	667	А
I _T	Continuous (direct) on-state current	-	595	А
Single Sid	e Cooled (Anode side)			
I _{T(AV)}	Mean on-state current	Half wave resistive load	285	А
I _{T(RMS)}	RMS value	-	447	Α
I _T	Continuous (direct) on-state current	-	360	А



SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	6.0	kA
l²t	I ² t for fusing	$V_R = 50\% V_{RRM} - 1/4 \text{ sine}$	0.18 x 10 ⁶	A²s
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	7.5	kA
l ² t	I ² t for fusing	$V_R = 0$	0.28 x 10 ⁶	A²s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
	Thermal resistance - junction to case	Double side cooled	dc	-	0.032	°C/W
$R_{th(j-c)}$		Single side cooled	Anode dc	-	0.064	°C/W
			Cathode dc	-	0.064	°C/W
R _{th(c-h)}	Thermaliesisiance - case to heatsink	Clamping force 12kN with mounting compound	Double side	-	0.008	°C/W
			Single side	-	0.016	°C/W
T _{vj}	Virtual junction temperature	On-state (conducting)		-	135	°C
		Reverse (blocking)		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
-	Clamping force			10.8	13.2	kN



DYNAMIC CHARACTERISTICS

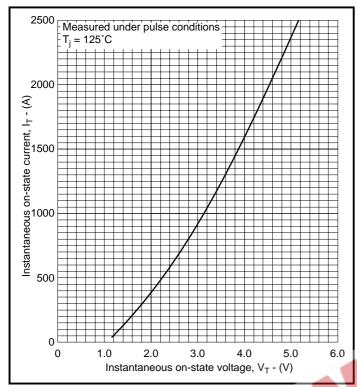
Symbol	Parameter	Conditions		Тур.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	50	mA
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% V _{DRM} T _j = 125°C.		-	1000	V/μs
all /alk	Data of visa of an about assument	Gate source 20V, 10Ω	Repetitive 50Hz	-	75	A/μs
dl/dt	Rate of rise of on-state current		Non-repetitive	-	150	A/μs
V _{T(TO)}	Threshold voltage	At T _{vj} = 125°C		-	1.4	V
r _T	On-state slope resistance	At T _{vj} = 125°C		-	1.7	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, Gate source 30V, 15Ω Rise time 0.5μs, $T_j = 25$ °C		-	1.7	μs
I _L	Latching current	$T_j = 25^{\circ}\text{C}, V_D = 5\text{V}, \text{ Gate source} = 20\text{V}, 10\Omega$		100	1000	mA
I _H	Holding current	$T_j = 25^{\circ}C$, $R_{g-k} = \infty$		60	500	mA
t _q	Turn-off time	$I_T = 1000A$, $t_p = 1$ ms, $T_1 = 125$ °C, $V_{RM} = 100V$, $dI_{RR}/dt = 10A/\mu$ s, $dV_{DR}/dt = 20V/\mu$ s to 3000V		450	-	μs

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions		Units
$V_{\rm GT}$	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C	3.0	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	300	mA
V _{GD}	Gate non-trigger voltage	At V _{DRM} T _{case} = 125°C	0.25	V
V_{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	30	V
V_{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	0.25	V
V_{RGM}	Peak reverse gate voltage		5	V
I _{FGM}	Peak forward gate current	Anode positive with respect to cathode	10	Α
P_{GM}	Peak gate power	See table, fig.5	150	W
$P_{G(AV)}$	Mean gate power		5	W



CURVES



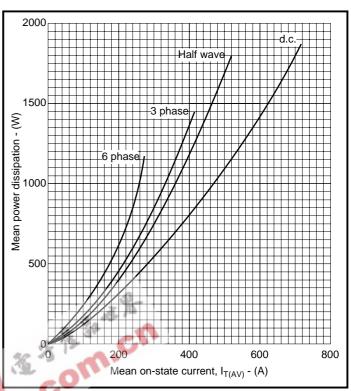


Fig.2 Maximum (limit) on-state characteristics

Fig.3 Dissipation curves

V_{TM} Equation:-

$$V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$$

Where A = 0.650046

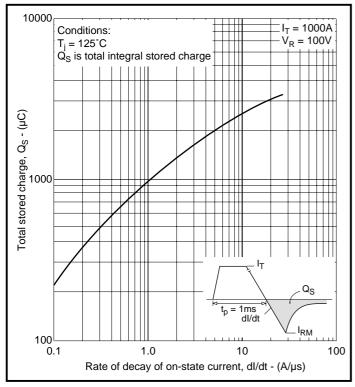
B = -0.018621

C = 0.000589

D = 0.063601

these values are valid for $T_j = 125^{\circ}C$ for $I_T 500A$ to 2500A





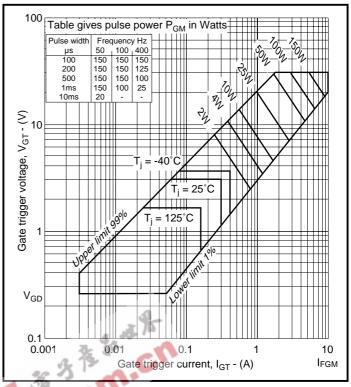


Fig.4 Stored charge

Fig.5 Gate characteristics

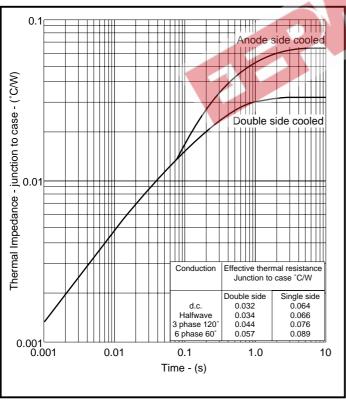


Fig.6 Transient thermal impedance - junction to case

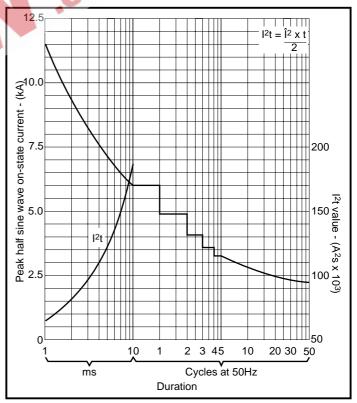
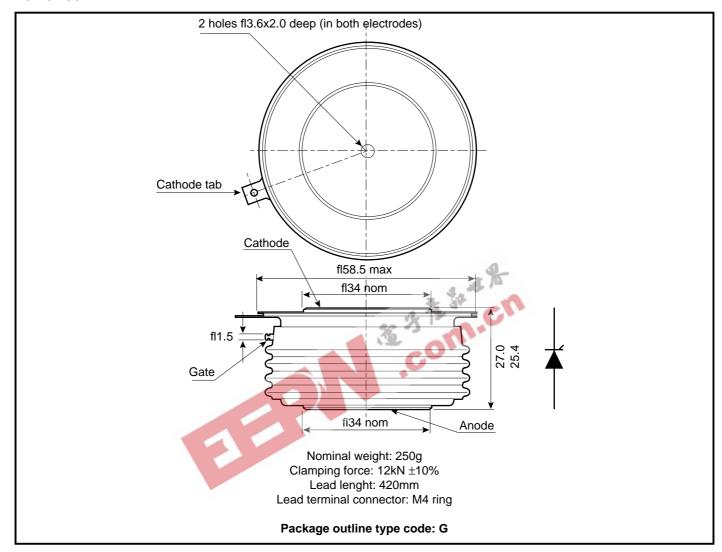


Fig.7 Surge (non-repetitive) on-state current vs time (with $50\% \ V_{RRM}$ at $T_{case} = 125^{\circ}C$)



PACKAGE DETAILS

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink / clamping systems in line with advances in device types and the voltage and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the up to date CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete solution (PACs).

DEVICE CLAMPS

Disc devices require the correct clamping force to ensure their safe operation. The PACs range offers a varied selection of pre-loaded clamps to suit all of our manufactured devices. This include cube clamps for single side cooling of 'T' 22mm

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

HEATSINKS

Power Assembly has its own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance or our semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest Sales Representative or Customer Services.



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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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